

Cheng Song

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Interface-Enhanced Ferromagnetism with Long-Distance Effect in van der Waals Semiconductor. Advanced Functional Materials, 2022, 32, 2108953.	14.9	13
2	SAW Filters With Excellent Temperature Stability and High Power Handling Using LiTaO ₃ /SiC Bonded Wafers. Journal of Microelectromechanical Systems, 2022, 31, 186-193.	2.5	10
3	An overview of SrRuO ₃ -based heterostructures for spintronic and topological phenomena. Journal Physics D: Applied Physics, 2022, 55, 233001.	2.8	15
4	Antiferromagnetic Magnon Drag Effect and Giant On-Off Ratio in a Vertical Device. Advanced Quantum Technologies, 2022, 5, .	3.9	2
5	Controllable Generation of Antiferromagnetic Skyrmions in Synthetic Antiferromagnets with Thermal Effect. Advanced Functional Materials, 2022, 32, .	14.9	16
6	Investigation of Temperature-Dependent Magnetic Properties and Coefficient of Thermal Expansion in Invar Alloys. Materials, 2022, 15, 1504.	2.9	2
7	Efficient orbital torque in polycrystalline $O_{3}Mn_3$ stacks: Theory and experiment. Physical Review B, 2022, 105, .	3.2	14
8	Control of vortex circulation in bistable ultra-small ferromagnetic nanodisk. Journal of Magnetism and Magnetic Materials, 2022, 551, 169092.	2.3	1
9	Polarization Evolution in Nanometer-Thick PbZrO ₃ Films: Implications for Energy Storage and Pyroelectric Sensors. ACS Applied Nano Materials, 2022, 5, 6083-6088.	5.0	5
10	Tunable Spin Hall Magnetoresistance in All-Antiferromagnetic Heterostructures. Chinese Physics Letters, 2022, 39, 047502.	3.3	3
11	High Chern number quantum anomalous Hall effect tunable by stacking order in van der Waals topological insulators. Physical Review B, 2022, 105, .	3.2	16
12	Observation of Spin Splitting Torque in a Collinear Antiferromagnet RuO ₂ . Physical Review Letters, 2022, 128, .	7.8	68
13	Piezoelectric Strain-Controlled Magnon Spin Current Transport in an Antiferromagnet. Nano Letters, 2022, 22, 4646-4653.	9.1	6
14	Implementation of Highly Reliable and Energy-Efficient Nonvolatile In-Memory Computing using Multistate Domain Wall Spin-Orbit Torque Device. Advanced Intelligent Systems, 2022, 4, .	6.1	13
15	A Low-Loss Wideband SAW Filter With Low Drift Using Multilayered Structure. IEEE Electron Device Letters, 2022, 43, 1371-1374.	3.9	8
16	Over GHz bandwidth SAW filter based on 32Å Y-X LN/SiO ₂ /poly-Si/Si heterostructure with multilayer electrode modulation. Applied Physics Letters, 2022, 120, .	3.3	22
17	Orthogonal interlayer coupling in an all-antiferromagnetic junction. Nature Communications, 2022, 13, .	12.8	7
18	Spin-orbit torques: Materials, mechanisms, performances, and potential applications. Progress in Materials Science, 2021, 118, 100761.	32.8	127

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19	Atomic insight into spin, charge and lattice modulations at SrFeO _{3-x} /SrTiO ₃ interfaces. <i>Nanoscale</i> , 2021, 13, 6066-6075.	5.6	9
20	Evolution of domain structure in Fe ₃ GeTe ₂ . <i>Chinese Physics B</i> , 2021, 30, 027505.	1.4	7
21	Observation of the antiferromagnetic spin Hall effect. <i>Nature Materials</i> , 2021, 20, 800-804.	27.5	113
22	Chiral Mesostructured NiO Films with Spin Polarisation. <i>Angewandte Chemie</i> , 2021, 133, 9507-9512.	2.0	1
23	Chiral Mesostructured NiO Films with Spin Polarisation. <i>Angewandte Chemie - International Edition</i> , 2021, 60, 9421-9426.	13.8	35
24	Study of spin mixing conductance of single oriented Pt in Pt/Ni ₈₁ Fe ₁₉ heterostructure by spin pumping. <i>AIP Advances</i> , 2021, 11, 035211.	1.3	2
25	Wideband and Low-Loss Surface Acoustic Wave Filter Based on 15° YX-LiNbO ₃ /SiO ₂ /Si Structure. <i>IEEE Electron Device Letters</i> , 2021, 42, 438-441.	3.9	73
26	Temperature dependence of spin-orbit torque-driven magnetization switching in <i>in situ</i> grown Bi ₂ Te ₃ /MnTe heterostructures. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	12
27	Widely tunable optical properties via oxygen manipulation in an amorphous alloy. <i>Science China Materials</i> , 2021, 64, 2305-2312.	6.3	4
28	Emerging opportunities for voltage-driven magneto-ionic control in ferroic heterostructures. <i>APL Materials</i> , 2021, 9, .	5.1	22
29	Reducing Dzyaloshinskii-Moriya interaction and field-free spin-orbit torque switching in synthetic antiferromagnets. <i>Nature Communications</i> , 2021, 12, 3113.	12.8	47
30	Insight into interlayer magnetic coupling in $\text{Mn}_{1-x}\text{Fe}_x\text{S}$ $\text{Mn}_{1-x}\text{Fe}_x\text{S}/\text{Mn}_{1-x}\text{Fe}_x\text{S}$ -type transition metal dichalcogenides based on the stacking of nonmagnetic atoms. <i>Physical Review B</i> , 2021, 103, .	3.2	7
31	Observation of negative capacitance in antiferroelectric PbZrO ₃ Films. <i>Nature Communications</i> , 2021, 12, 4215.	12.8	22
32	Enhanced Coupling Coefficient in Dual-Mode ZnO/SiC Surface Acoustic Wave Devices with Partially Etched Piezoelectric Layer. <i>Applied Sciences (Switzerland)</i> , 2021, 11, 6383.	2.5	10
33	Plasma Etching-Assisted Perpendicular Magnetic Anisotropy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2100368.	1.8	1
34	Near 30% fractional bandwidth surface acoustic wave filters with novel electrode configuration. <i>Progress in Natural Science: Materials International</i> , 2021, 31, 852-857.	4.4	9
35	Designing All-inorganic EuO-Sensitized TiO ₂ Solar Cell from 4f-3d Composite Bandgap Structure. <i>Advanced Theory and Simulations</i> , 2021, 4, 2100235.	2.8	2
36	Structure with thin SiO _x /SiN _x bilayer and Al electrodes for high-frequency, large-coupling, and low-cost surface acoustic wave devices. <i>Ultrasonics</i> , 2021, 115, 106460.	3.9	6

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37	Spin-Dependent Charge Transport in 1D Chiral Hybrid Lead-Bromide Perovskite with High Stability. Advanced Functional Materials, 2021, 31, 2104605.	14.9	44
38	Temperature-Dependent Terahertz Emission from Co/Mn 2 Au Spintronic Bilayers. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100290.	2.4	10
39	A Multilayered Structure for Packageless Acoustic-Wave Devices With Ultra-Small Sizes. Journal of Microelectromechanical Systems, 2021, 30, 589-596.	2.5	7
40	High-Performance Surface Acoustic Wave Devices Using LiNbO ₃ /SiO ₂ /SiC Multilayered Substrates. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 3693-3705.	4.6	67
41	Control of spin-orbit torques through magnetic symmetry in differently oriented noncollinear antiferromagnetic $\text{Mn}_3\text{Mn}_{18}$. Physical Review B, 2021, 104, .		
42	Noble-Metal-Assisted Fast Interfacial Oxygen Migration with Topotactic Phase Transition in Perovskite Oxides. Advanced Functional Materials, 2021, 31, 2106765.	14.9	18
43	Highly Efficient Spin-Filtering Transport in Chiral Hybrid Copper Halides. Angewandte Chemie, 2021, 133, 23770.	2.0	1
44	Highly Efficient Spin-Filtering Transport in Chiral Hybrid Copper Halides. Angewandte Chemie - International Edition, 2021, 60, 23578-23583.	13.8	43
45	Systematical Study of the Basic Properties of Surface Acoustic Wave Devices Based on ZnO and GaN Multilayers. Electronics (Switzerland), 2021, 10, 23.	3.1	15
46	Facilitating room-temperature oxygen ion migration <i>via</i> Co-O bond activation in cobaltite films. Nanoscale, 2021, 13, 18256-18266.	5.6	8
47	Ultra-Wideband Surface Acoustic Wave Filters Based on the Cu/LiNbO ₃ /SiO ₂ /SiC Structure. , 2021, .		3
48	Basic Logic Operations Achieved in a Single 2D WSe ₂ Transistor by Surface-Charge-Transfer Doping. ACS Applied Electronic Materials, 2021, 3, 5059-5065.	4.3	1
49	Terahertz pulse-induced Néel vector switching in $\text{Fe}_2\text{O}_3/\text{Pt}$ heterostructures. Applied Physics Letters, 2021, 119, 212401.	3.3	7
50	Cluster magnetic octupole induced out-of-plane spin polarization in antiperovskite antiferromagnet. Nature Communications, 2021, 12, 6524.	12.8	34
51	Bias-dependent tunneling anisotropic magnetoresistance in antiferromagnetic Pd-doped FeRh-based junctions. Applied Physics Letters, 2021, 119, .	3.3	2
52	Charge-magnon conversion at the topological insulator/antiferromagnetic insulator interface. Physical Review B, 2020, 102, .	3.2	2
53	Design of a Controllable Redox-Diffusive Threshold Switching Memristor. Advanced Electronic Materials, 2020, 6, 2000695.	5.1	43
54	3D Layout of Interdigital Transducers for High Frequency Surface Acoustic Wave Devices. IEEE Access, 2020, 8, 123262-123271.	4.2	16

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55	Formation and annihilation of multi-antiskyrmion defects during skyrmion nucleation. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	1
56	Tunable spin-orbit torque switching in antiferromagnetically coupled CoFeB/Ta/CoFeB. <i>Applied Physics Letters</i> , 2020, 117, 212403.	3.3	10
57	Quantum anomalous Hall insulator state in ferromagnetically ordered $\text{Mn}_{3/2}\text{Bi}_{3/2}\text{Te}_{2/3}$ heterostructures. <i>Physical Review B</i> , 2020, 102, .	3.2	25
58	Ultrafast electron transport in metallic antiferromagnetic Mn2Au thin films probed by terahertz spectroscopy. <i>Physical Review B</i> , 2020, 102, .	3.2	4
59	Electrical control goes to topological antiferromagnets. <i>Science China: Physics, Mechanics and Astronomy</i> , 2020, 63, 1.	5.1	0
60	Thermal generation, manipulation and thermoelectric detection of skyrmions. <i>Nature Electronics</i> , 2020, 3, 672-679.	26.0	86
61	Enhanced Performance of ZnO/SiO ₂ /Al ₂ O ₃ Surface Acoustic Wave Devices with Embedded Electrodes. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 42378-42385.	8.0	17
62	Size-dependent anomalous Hall effect in noncollinear antiferromagnetic Mn ₃ Sn films. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	22
63	Exchange Bias in Antiferromagnetic $\text{Mn}_{3/2}\text{Sn}_{3/2}\text{Te}_{7/8}$ Monolayer Films. <i>Physical Review Applied</i> , 2020, 14, .	3.8	17
64	Highly Efficient Electric-Field Control of Giant Rashba Spin-orbit Coupling in Lattice-Matched InSb/CdTe Heterostructures. <i>ACS Nano</i> , 2020, 14, 17396-17404.	14.6	15
65	Functional antiferromagnets for potential applications on high-density storage and high frequency. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	18
66	Room temperature anomalous Hall effect in antiferromagnetic Mn ₃ SnN films. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	20
67	Performance Improvement of Conductive Bridging Random Access Memory by Electrode Alloying. <i>Journal of Physical Chemistry C</i> , 2020, 124, 11438-11443.	3.1	9
68	Cluster-Type Filaments Induced by Doping in Low-Operation-Current Conductive Bridge Random Access Memory. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 29481-29486.	8.0	4
69	Current-induced magnetization switching in a CoTb amorphous single layer. <i>Physical Review B</i> , 2020, 101, .	3.2	59
70	Current-Induced In-Plane Magnetization Switching in a Biaxial Ferrimagnetic Insulator. <i>Physical Review Applied</i> , 2020, 13, .	3.8	14
71	Magnetic field direction dependence of topological Hall effect like features in synthetic ferromagnetic and antiferromagnetic multilayers. <i>Applied Physics Letters</i> , 2020, 116, 242403.	3.3	9
72	High-frequency and high-temperature stable surface acoustic wave devices on ZnO/SiO ₂ /SiC structure. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 305102.	2.8	12

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73	Imaging Magnetization Switching Induced by Spin-Orbit Torque in Perpendicularly Magnetized Ta/CoFeB Structure. <i>IEEE Transactions on Magnetics</i> , 2020, 56, 1-6.	2.1	0
74	Highâ€Performance Optoelectronics: Lateral 2D WSe ₂ pâ€n Homojunction Formed by Efficient Chargeâ€Carrierâ€Type Modulation for Highâ€Performance Optoelectronics (<i>Adv. Mater.</i> 9/2020). <i>Advanced Materials</i> , 2020, 32, 2070067.	21.0	2
75	Tailoring the Hybrid Anomalous Hall Response in Engineered Magnetic Topological Insulator Heterostructures. <i>Nano Letters</i> , 2020, 20, 1731-1737.	9.1	26
76	Spin pumping during the antiferromagneticâ€“ferromagnetic phase transition of ironâ€“rhodium. <i>Nature Communications</i> , 2020, 11, 275.	12.8	41
77	Interfacial Control of Ferromagnetism in Ultrathin SrRuO ₃ Films Sandwiched between Ferroelectric BaTiO ₃ Layers. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 6707-6715.	8.0	16
78	Lateral 2D WSe ₂ pâ€n Homojunction Formed by Efficient Chargeâ€Carrierâ€Type Modulation for Highâ€Performance Optoelectronics. <i>Advanced Materials</i> , 2020, 32, e1906499.	21.0	103
79	Realization of Isolated and High-Density Skyrmions at Room Temperature in Uncompensated Synthetic Antiferromagnets. <i>Nano Letters</i> , 2020, 20, 3299-3305.	9.1	42
80	A comparative study of spin Hall magnetoresistance in Fe ₂ O ₃ -based systems. <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	10
81	Orientation control of oxygen vacancy channels in brownmillerite $\text{SrFe}_{2.5}\text{O}_{4.1}$. <i>Physical Review Materials</i> , 2020, 4, .		
82	Interfacial oxygen-octahedral-tilting-driven electrically tunable topological Hall effect in ultrathin SrRuO ₃ films. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 404001.	2.8	51
83	Electric field control of NÃ©el spinâ€“orbit torque in an antiferromagnet. <i>Nature Materials</i> , 2019, 18, 931-935.	27.5	132
84	Tuning the magnetotransport behavior of topological insulator with a transition-metal oxide layer. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 405001.	1.8	2
85	Electric and Light Dual-Gate Tunable MoS ₂ Memtransistor. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 43344-43350.	8.0	51
86	Orientation-dependent THz emission in non-collinear antiferromagnetic Mn ₃ Sn and Mn ₃ Sn-based heterostructures. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	25
87	Simultaneous detection of the spin Hall magnetoresistance and Joule heating-induced spin Seebeck effect in Gd ₃ Fe ₅ O ₁₂ /Pt bilayers. <i>Journal of Applied Physics</i> , 2019, 126, .	2.5	7
88	Strong magnetoresistance modulation by Ir insertion in a Ta/Ir/CoFeB trilayer. <i>Physical Review B</i> , 2019, 100, .	3.2	6
89	Magnetic field direction dependent magnetization reversal in synthetic antiferromagnets. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	12
90	Electric Field Control of Phase Transition and Tunable Resistive Switching in SrFeO _{2.5} . <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 6581-6588.	8.0	45

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91	Modulating metallic conductive filaments via bilayer oxides in resistive switching memory. <i>Applied Physics Letters</i> , 2019, 114, 193502.	3.3	37
92	From Fieldlike Torque to Antidamping Torque in Antiferromagnetic $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll">\langle mml:msub>\langle mml:mi>Mn</mml:mi>\langle mml:mn>2</mml:mn>\langle mml:msub>\langle mml:mi>Au</mml:mi>\langle mml:mi>^{3+}\langle mml:math>$. <i>Physical Review Applied</i> , 2019, 11, .	3.8	36
93	Oxygen-Valve Formed in Cobaltite-Based Heterostructures by Ionic Liquid and Ferroelectric Dual-Gating. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 19584-19595.	8.0	30
94	Spin valve effect induced by spin-orbit torque switching. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	4
95	Nonvolatile Memory: Performance-Enhancing Selector via Symmetrical Multilayer Design (Adv. Funct.) $T_f = ETQq_1 \frac{1}{14.9} \cdot \frac{784314}{rgBT} \cdot \frac{1}{C_{over}}$	1.0	7
96	High-frequency V-doped ZnO/SiC surface acoustic wave devices with enhanced electromechanical coupling coefficient. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	21
97	Anomalous Hall Effect-Like Behavior with In-Plane Magnetic Field in Noncollinear Antiferromagnetic Mn ₃ Sn Films. <i>Advanced Electronic Materials</i> , 2019, 5, 1800818.	5.1	56
98	Electrical Control of Anisotropic Ferromagnetic Domains During Antiferromagnetic-Ferromagnetic Phase Transition. <i>Physical Review Applied</i> , 2019, 11, .	3.8	4
99	Simulation of temperature compensated waveguiding layer acoustic wave devices. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 075105.	2.8	7
100	High-Frequency Surface Acoustic Wave Devices Based on ZnO/SiC Layered Structure. <i>IEEE Electron Device Letters</i> , 2019, 40, 103-106.	3.9	45
101	Performance-Enhancing Selector via Symmetrical Multilayer Design. <i>Advanced Functional Materials</i> , 2019, 29, 1808376.	14.9	56
102	Behavior of Al/Cu/Ti electrodes in surface acoustic wave filter at high power. <i>Current Applied Physics</i> , 2019, 19, 363-369.	2.4	6
103	Facile access to shape-controlled growth of WS ₂ monolayer via environment-friendly method. <i>2D Materials</i> , 2019, 6, 015007.	4.4	18
104	Grain Size-Dependent Mechanical Properties of a High-Manganese Austenitic Steel. <i>Acta Metallurgica Sinica (English Letters)</i> , 2019, 32, 746-754.	2.9	30
105	Enhanced power durability of surface acoustic wave filter with Al/Ti/Cu/Ti electrodes. <i>Journal of Alloys and Compounds</i> , 2018, 740, 222-228.	5.5	10
106	Competition between Metallic and Vacancy Defect Conductive Filaments in a CH ₃ NH ₃ PbI ₃ -Based Memory Device. <i>Journal of Physical Chemistry C</i> , 2018, 122, 6431-6436.	3.1	115
107	Microstructure and interfacial strength of SiC fiber-reinforced Ti17 alloy composites with different consolidation temperatures. <i>Rare Metals</i> , 2018, 37, 759-768.	7.1	13
108	Controllable oxygen vacancies, orbital occupancy and magnetic ordering in SrCoO ₃ films. <i>Journal of Magnetism and Magnetic Materials</i> , 2018, 454, 228-236.	2.3	13

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109	Texture-enhanced Al-Cu electrodes on ultrathin Ti buffer layers for high-power durable 2.6 GHz SAW filters. <i>AIP Advances</i> , 2018, 8, 045212.	1.3	11
110	Improving Unipolar Resistive Switching Uniformity with Cone-Shaped Conducting Filaments and Its Logic-In-Memory Application. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 6453-6462.	8.0	68
111	Electric-field control of ferromagnetism in a Co-Fe-Ta-B amorphous alloy. <i>Materials and Design</i> , 2018, 143, 65-71.	7.0	7
112	How to manipulate magnetic states of antiferromagnets. <i>Nanotechnology</i> , 2018, 29, 112001.	2.6	79
113	Enhanced SAW characteristics of a-plane AlN epitaxial films using ZnO buffer layer. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 3912-3919.	2.2	14
114	Giant Tunnel Magnetoresistance with a Single Magnetic Phase-Transition Electrode. <i>Physical Review Applied</i> , 2018, 9, .	3.8	7
115	Characteristics of one-port surface acoustic wave resonator fabricated on ZnO/6H-SiC layered structure. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 145305.	2.8	12
116	Evolution of microstructures and mechanical properties during solution treatment of a Tiâ€“Mo-containing highâ€“manganese cryogenic steel. <i>Materials Characterization</i> , 2018, 135, 287-294.	4.4	26
117	Local Control of Exchange Bias by Resistive Switching. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018, 12, 1800446.	2.4	8
118	Magnetic Proximity Effect and Anomalous Hall Effect in $\text{Y}_{\text{3}}\text{Fe}_5\text{O}_8$. <i>Physical Review Applied</i> , 2018, 10, .	3.8	12
119	Control of Secondary Phases by Solution Treatment in a N-Alloyed High-Mn Cryogenic Steel. <i>Acta Metallurgica Sinica (English Letters)</i> , 2018, 31, 1059-1072.	2.9	2
120	Antidamping-Torque-Induced Switching in Biaxial Antiferromagnetic Insulators. <i>Physical Review Letters</i> , 2018, 120, 207204.	7.8	246
121	Strong Orientation-Dependent Spin-Orbit Torque in Thin Films of the Antiferromagnet $\text{Mn}_{1-x}\text{Fe}_{x}$. <i>Physical Review Applied</i> , 2018, 9, .	3.8	75
122	Light Tuning of the Resistance of NdNiO_3 Films With CoFe ₂ O ₄ Capping. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018, 12, 1800186.	2.4	2
123	Improved resistance to electromigration and acoustomigration of Al interdigital transducers by Ni underlayer. <i>Rare Metals</i> , 2018, 37, 823-830.	7.1	10
124	Spin-orbit torque in a completely compensated synthetic antiferromagnet. <i>Physical Review B</i> , 2018, 97, .	3.2	73
125	Optimization of C/TiC duplex diffusion barrier coatings for SiC /Ti composites based on interfacial structure evolution exploration. <i>Ceramics International</i> , 2018, 44, 16528-16534.	4.8	4
126	Role of an ultrathin platinum seed layer in antiferromagnet-based perpendicular exchange coupling and its electrical manipulation. <i>Journal of Magnetism and Magnetic Materials</i> , 2017, 428, 431-436.	2.3	8

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127	Robust Interfacial Exchange Bias and Metal–Insulator Transition Influenced by the LaNiO ₃ Layer Thickness in La _{0.7} Sr _{0.3} MnO ₃ /LaNiO ₃ Superlattices. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 3156-3160.	8.0	31
128	Lateral transport properties of thermally excited magnons in yttrium iron garnet films. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	22
129	Recent progress in voltage control of magnetism: Materials, mechanisms, and performance. <i>Progress in Materials Science</i> , 2017, 87, 33-82.	32.8	357
130	Spintronic materials and devices based on antiferromagnetic metals. <i>Progress in Natural Science: Materials International</i> , 2017, 27, 208-216.	4.4	31
131	Spin-orbit torque in MgO/CoFeB/Ta/CoFeB/MgO symmetric structure with interlayer antiferromagnetic coupling. <i>Physical Review B</i> , 2017, 95, .	3.2	82
132	Metal-insulator-metal transition in NdNiO ₃ films capped by CoFe ₂ O ₄ . <i>Applied Physics Letters</i> , 2017, 110, .	3.3	12
133	Electric-Field Control of Oxygen Vacancies and Magnetic Phase Transition in a Cobaltite/Manganite Bilayer. <i>Physical Review Applied</i> , 2017, 8, .	3.8	32
134	Terahertz Spin Currents and Inverse Spin Hall Effect in Thin-Film Heterostructures Containing Complex Magnetic Compounds. <i>Spin</i> , 2017, 07, 1740010.	1.3	65
135	Sputtering power dependence of structure and photoluminescence of ZnO on 6H-SiC. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 17881-17888.	2.2	5
136	Spin-orbit torque switching in MgO/CoFeB/Ta/CoFeB/MgO heterostructures with a critical current density of 10 ⁵ A/cm ² . <i>Japanese Journal of Applied Physics</i> , 2017, 56, 100303.	1.5	4
137	Guiding the Growth of a Conductive Filament by Nanoindentation To Improve Resistive Switching. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 34064-34070.	8.0	106
138	Tunneling anisotropic magnetoresistance driven by magnetic phase transition. <i>Nature Communications</i> , 2017, 8, 449.	12.8	49
139	Hall detection of anisotropic domain walls during magnetic phase transition. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 505004.	2.8	5
140	Temperature-dependent transport properties of FeRh. <i>Physical Review B</i> , 2017, 95, .	3.2	22
141	Transparent magnetic semiconductor with embedded metallic glass nano-granules. <i>Materials and Design</i> , 2017, 132, 208-214.	7.0	16
142	Time Resolved Measurements of the Switching Trajectory of $\text{Pt}_{\text{Mn}}/\text{Co}/\text{Co}_{\text{Mn}}$ Elements Induced by Spin-Orbit Torques. <i>Physical Review Letters</i> , 2017, 118, 257201.	7.8	37
143	Photon-gated Spin Transistor. <i>Advanced Materials</i> , 2017, 29, 1604052.	21.0	12
144	Chemical modulation of electronic structure at the excited state. <i>Physical Review B</i> , 2017, 96, .	3.2	1

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145	Detection of magnetic circular dichroism in amorphous materials utilizing a single-crystalline overlayer. <i>Physical Review Materials</i> , 2017, 1, .	2.4	6
146	Electrical control of antiferromagnetic metal up to 15 nm. <i>Science China: Physics, Mechanics and Astronomy</i> , 2016, 59, 1.	5.1	8
147	Manipulation of Electric Field Effect by Orbital Switch. <i>Advanced Functional Materials</i> , 2016, 26, 753-759.	14.9	49
148	A room-temperature magnetic semiconductor from a ferromagnetic metallic glass. <i>Nature Communications</i> , 2016, 7, 13497.	12.8	71
149	Unipolar resistive switching with forming-free and self-rectifying effects in Cu/HfO ₂ /n-Si devices. <i>AIP Advances</i> , 2016, 6, .	1.3	19
150	Electrochemical control of the phase transition of ultrathin FeRh films. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	27
151	Strong Electrical Manipulation of Spin-Orbit Torque in Ferromagnetic Heterostructures. <i>Advanced Electronic Materials</i> , 2016, 2, 1600219.	5.1	37
152	Insight into the antiferromagnetic structure manipulated by electronic reconstruction. <i>Physical Review B</i> , 2016, 94, .	3.2	16
153	Vertical Spin Hall Magnetoresistance in $T_{\text{mi}} \times P_{\text{mi}}^{3/2} / \text{YIG}$ films by orbital polarization. <i>Physical Review B</i> , 2016, 93, .	3.2	16
154	Optical control of magnetism in manganite films. <i>Physical Review B</i> , 2016, 93, .	3.2	10
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